NSN 5961-01-374-7150

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Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-374-7150 **Inclosure Material:** Plastic **Overall Length:** Between 2.8 millimeters and 3.0 millimeters **Overall Height:** 1.1 millimeters **Overall Width:** Between 1.2 millimeters and 1.4 millimeters Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-23 **Mounting Method: Terminal Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 28.0 emitter to collector voltage, floating potential, dc with base biased in reverse direction with respect to the collector **Current Rating Per Characteristic:** 10.00 nanoamperes operating voltage dc peak **Capacitance Rating In Picofarads:** Between 3.8 and 4.8 **Maximum Operating Tempurature Per Measurement Point:** 85.0 degrees celsius junction **Special Features:** Third lead not connected; junction pattern arrangement: pn **Terminal Type And Quantity:** 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No